

1-of-16 Decoder/Demultiplexer High-Performance Silicon-Gate CMOS

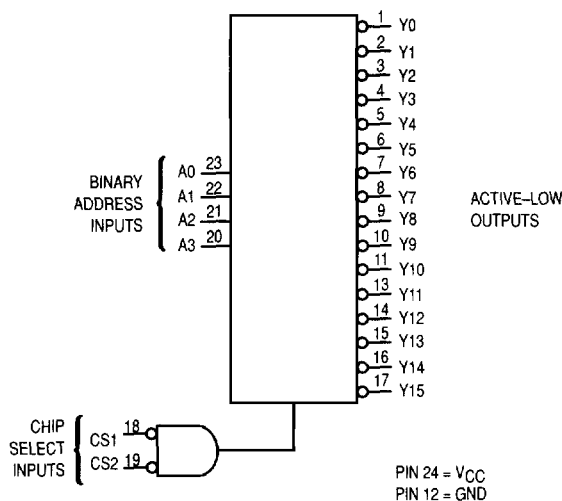
The MC54/74HC154 is identical in pinout to the LS154. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This device, when enabled, selects one of 16 active-low outputs. Two active-low Chip Selects are provided to facilitate the chip-select, demultiplexing, and cascading functions. When either Chip Select is high, all outputs are high. The demultiplexing function is accomplished by using the Address inputs to select the desired device output. Then, while holding one chip select input low, data can be applied to the other chip select input (see Application Note).

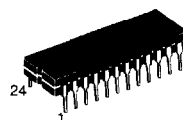
The HC154 is primarily used for memory address decoding and data routing applications.

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2 to 6 V
- Low Input Current: 1 μ A
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 192 FETs or 48 Equivalent Gates

LOGIC DIAGRAM



MC54/74HC154



J SUFFIX
CERAMIC PACKAGE
CASE 758-02



N SUFFIX
PLASTIC PACKAGE
CASE 724-03



DW SUFFIX
SOIC PACKAGE
CASE 751E-04

ORDERING INFORMATION

MC54HCXXXJ	Ceramic
MC74HCXXXN	Plastic
MC74HCXXXDW	SOIC

PIN ASSIGNMENT

Y0	1	24	VCC
Y1	2	23	A0
Y2	3	22	A1
Y3	4	21	A2
Y4	5	20	A3
Y5	6	19	CS2
Y6	7	18	CS1
Y7	8	17	Y15
Y8	9	16	Y14
Y9	10	15	Y13
Y10	11	14	Y12
GND	12	13	Y11

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MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V_{in}	DC Input Voltage (Referenced to GND)	- 1.5 to $V_{CC} + 1.5$	V
V_{out}	DC Output Voltage (Referenced to GND)	- 0.5 to $V_{CC} + 0.5$	V
I_{in}	DC Input Current, per Pin	± 20	mA
I_{out}	DC Output Current, per Pin	± 25	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	± 50	mA
P_D	Power Dissipation in Still Air, Plastic or Ceramic DIP† SOIC Package†	750 500	mW
T_{stg}	Storage Temperature	- 65 to + 150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP) (Ceramic DIP or SOIC Package)	260 300	°C

* Maximum Ratings are those values beyond which damage to the device may occur.

Functional operation should be restricted to the Recommended Operating Conditions.

† Derating — Plastic DIP: - 10 mW/°C from 65° to 125°C

Ceramic DIP: - 10 mW/°C from 100° to 125°C

SOIC Package: - 7 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $GND \leq (V_{in} \text{ or } V_{out}) \leq V_{CC}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V_{in}, V_{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V_{CC}	V
T_A	Operating Temperature, All Package Types	- 55	+ 125	°C
t_r, t_f	Input Rise and Fall Time (Figure 2)	$V_{CC} = 2.0 \text{ V}$ $V_{CC} = 4.5 \text{ V}$ $V_{CC} = 6.0 \text{ V}$	0 1000 500 400	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V_{CC} V	Guaranteed Limit			Unit
				- 55 to 25°C	≤ 85°C	≤ 125°C	
V_{IH}	Minimum High-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \leq 20 \mu\text{A}$	2.0	1.5	1.5	1.5	V
			4.5	3.15	3.15	3.15	
			6.0	4.2	4.2	4.2	
V_{IL}	Maximum Low-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \leq 20 \mu\text{A}$	2.0	0.3	0.3	0.3	V
			4.5	0.9	0.9	0.9	
			6.0	1.2	1.2	1.2	
V_{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \leq 20 \mu\text{A}$	2.0	1.9	1.9	1.9	V
			4.5	4.4	4.4	4.4	
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \leq 4.0 \text{ mA}$ $ I_{out} \leq 5.2 \text{ mA}$	6.0	5.9	5.9	5.9	
			4.5	3.98	3.84	3.70	
V_{OL}	Maximum Low-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \leq 20 \mu\text{A}$	2.0	0.1	0.1	0.1	V
			4.5	0.1	0.1	0.1	
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \leq 4.0 \text{ mA}$ $ I_{out} \leq 5.2 \text{ mA}$	6.0	0.1	0.1	0.1	
			4.5	0.26	0.33	0.40	
I_{in}	Maximum Input Leakage Current	$V_{in} = V_{CC} \text{ or GND}$	6.0	± 0.1	± 1.0	± 1.0	μA
			6.0	8	80	160	
I_{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC} \text{ or GND}$ $I_{out} = 0 \mu\text{A}$	6.0	8	80	160	μA

NOTE: Information on typical parametric values can be found in Chapter 2.

SWITCHING WAVEFORMS

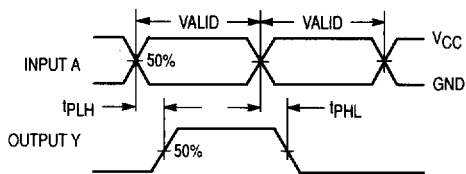


Figure 1.

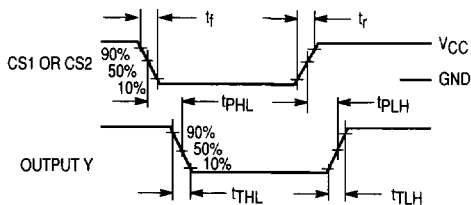
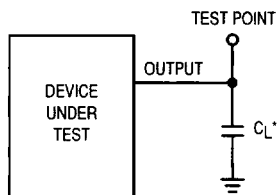


Figure 2.

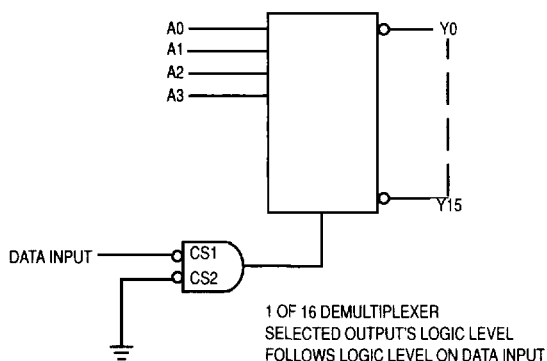
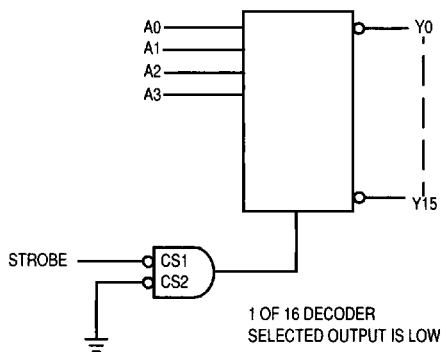


* Includes all probe and jig capacitance

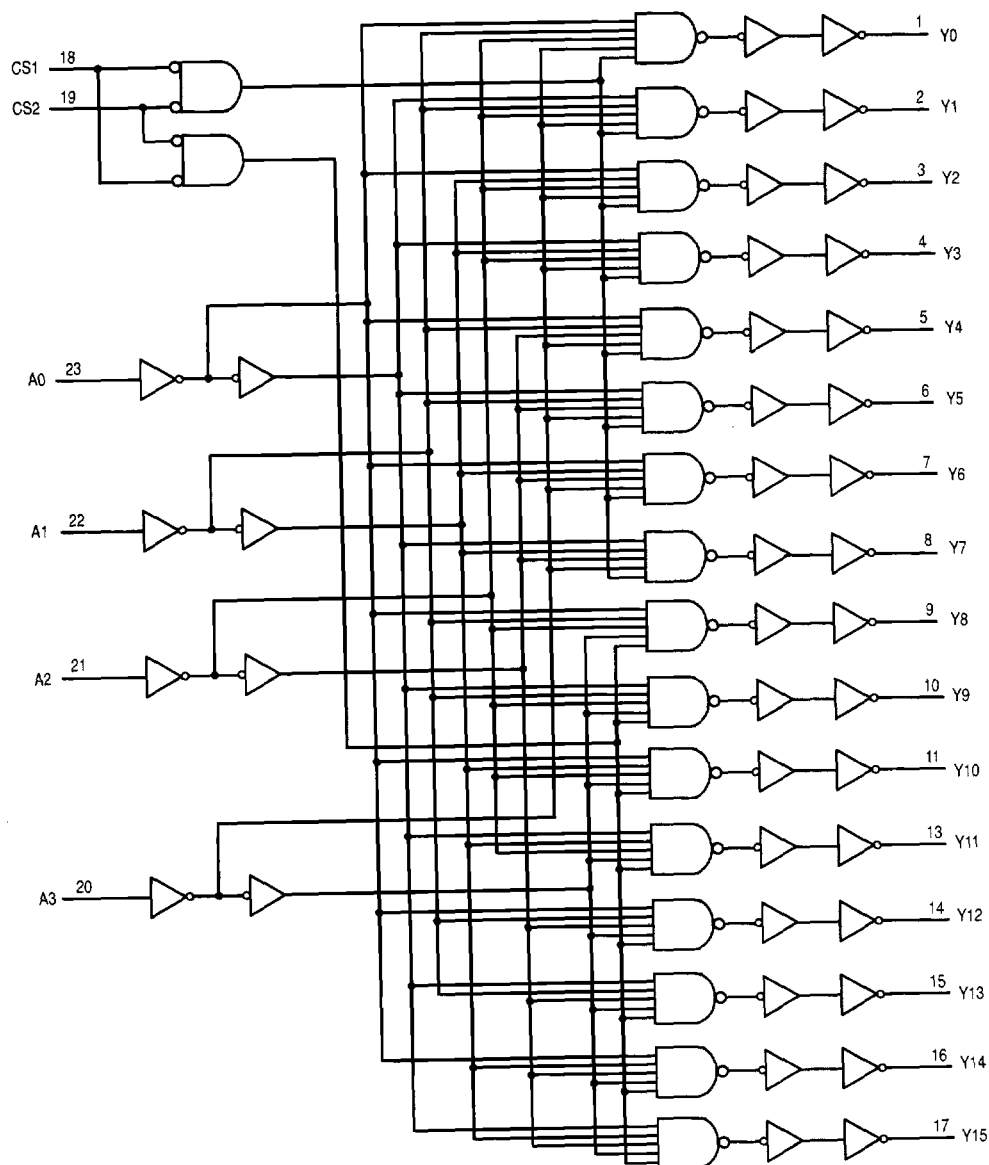
Figure 3. Test Circuit

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TYPICAL APPLICATIONS



EXPANDED LOGIC DIAGRAM

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